

**Curriculum Vitae**  
**Daniel F. Feezell**  
dfeezell@unm.edu

**Education:**

**Ph.D. Electrical Engineering**, University of California Santa Barbara, 2005

*Advisor:* Professor Larry A. Coldren

*Dissertation Title:* *Long-Wavelength Vertical-Cavity Surface-Emitting Lasers with Selectively Etched Thin Apertures*

**M.S. Electrical Engineering**, University of California Santa Barbara, 2001

**B.S. Electrical Engineering**, University of California Irvine, 2000

**Research Experience:**

**Assistant Professor - University of New Mexico, Electrical and Computer Engineering Department: 08/2012 – present**

- Epitaxial growth, fabrication, and characterization of group III-nitride materials and devices, including nonpolar/semipolar orientations. Solid-state lighting and high-efficiency LEDs. Visible edge-emitting and vertical-cavity surface-emitting lasers. III-nitride power electronics. Nonpolar intersubband photodetectors. Nanoscale epitaxial growth.

**Project Scientist - University of California Santa Barbara, Materials Department and Solid-State Lighting and Energy Center: 10/2010 – 08/2012**

- Managed light-emitting diode (LED) and laser diode (LD) projects in the Solid State Lighting and Energy Center (SSLEC)
- Mentored and provide direction to graduate students working on LED and LD projects in the SSLEC
- Composed funding proposals, technical publications, and conference presentations
- Performed metal-organic chemical-vapor deposition (MOCVD) of GaN-based materials
- Performed simulation, fabrication, and characterization of GaN-based materials and devices

**Senior Device Scientist (first employee) - Soraa/Kaai, Inc.: 12/2007 – 08/2010**

- Presented technology path to potential funding sources (venture capitalists, strategic partners, government agencies)
- Composed successfully funded proposals to Department of Energy (DOE) and Small Business Innovation Research (SBIR) program
- Served as co-principal investigator of DOE contract examining internal quantum efficiency (IQE) of nonpolar GaN-based LEDs
- Served as co-principal investigator of Defense Advanced Research Projects Agency (DARPA) sub-contract (through Ostendo Technologies) developing 485 nm LDs
- Co-led build-out of \$4 million fabrication facility, including tool specification and qualification
- Designed device architecture and led front-end process development for 1<sup>st</sup> generation GaN-based LED products (led team of 5 people)
- Performed optical, electrical, and structural characterization of GaN-based LEDs and materials
- Performed optical and electrical modeling of GaN-based LEDs and materials

**Postdoctoral Researcher - University of California Santa Barbara, Materials Department (Advisor: Shuji Nakamura): 09/2005 – 12/2007**

- Developed initial nonpolar/semipolar GaN-based LDs and LEDs (performed design, fabrication, and characterization)

- Developed AlGaIn-Cladding-Free LD structure using nonpolar GaN
- Developed GaN-based vertical-cavity surface-emitting laser (VCSEL) structure with dielectric distributed Bragg reflectors (DBRs), novel current spreading layer, and sapphire microlenses
- Composed funding proposals, technical publications, and conference presentations on nonpolar/semipolar GaN technology
- Mentored graduate students

**Graduate Student Research Assistant - University of California Santa Barbara, Electrical and Computer Engineering Department (Advisor: Larry Coldren): 08/2000 – 09/2005**

- Developed all-epitaxial InP-based 1310-1550 nm VCSELs with selectively-etched thin optical apertures and tunnel junctions (performed design, fabrication, and characterization)
- Demonstrated first continuous-wave operation and small-signal modulation of 1310 nm VCSELs with Sb-based DBRs and achieved record-high differential efficiency (>60%)

**Undergraduate Research Assistant - University of California Irvine (Advisor: Henry Lee): 09/1999 – 08/2000**

- Developed ohmic contacts to p-type GaN
- Performed optical and electrical characterization of GaN-based LEDs

**Teaching and Advising Experience:**

**Students advised** - Mohsen Nami (PhD advisor), Saadat Mishkat Ul-Masabih (PhD advisor), Emmanuel Mercado (MS committee), Tony Liu (MS committee), Jesse Mee (PhD committee), Huiwen Xu (PhD committee)

**Instructor - University of New Mexico: 01/2013 – 05/2013**

- Fundamentals of Semiconductor Lasers and LEDs (ECE 577): Spring 2013

**Instructor - University of California Santa Barbara: 01/2011 – 06/2011**

- Semiconductor Device Processing for III-Nitride LEDs and LDs (MAT 215C): Spring 2011
- Fundamentals of Solid State Physics (ECE 162B): Winter 2010 (co-taught)

**Academic Advisor - University of California Santa Barbara: 10/2010 – 08/2012**

- Two undergraduate students in senior research projects (test automation)
- Two graduate students in master's research projects (PEC etching of GaN and ITO contacts)
- Several graduate students in Ph.D. research projects (GaN-based LEDs and LDs)

**Guest Lecturer - University of California Santa Barbara: 09/2005 – 12/2007**

- Photonic devices and semiconductor processing classes for Professor Shuji Nakamura

**Nanotechnology (NNIN) Instructor - University of California Santa Barbara: 09/2004 – 06/2005**

- Introduced community college and high school students to applications for nanotechnology
- Developed course material, led discussions, and instructed students in lab exercises

**Teaching Assistant - University of California Santa Barbara: 09/2004 – 06/2005**

- Led discussion sessions and laboratories in semiconductor device processing courses
- Developed lab exercises, graded exams, and generated homework solutions

**Physics Instructor - Kaplan Test Prep: 09/2003 – 06/2005**

- Taught introductory physics to students preparing for the MCAT exam

**Teaching Assistant - University of California Irvine: 03/2003 – 06/2003**

- Designed labs and led discussions for undergraduate microelectronics class

### **Consulting Experience:**

#### **Expert Consultant – Williams & Connolly, LLP: 05/2013 – present**

- Provide technical expertise in solid-state lighting and LED devices

#### **Expert Consultant - Skadden, Arps, Slate, Meagher, and Flom, LLP: 09/2011 – present**

- Provided technical expertise in solid-state lighting and LED devices for ongoing patent litigation

#### **Expert Consultant - Insite Partners: 08/2010 – 11/2010**

- Provided technical expertise in GaN-based LDs for venture capital due diligence case

### **Awards and Honors:**

- DARPA Young Faculty Award for “High-Speed Nonpolar InGaN/GaN Light-Emitting Diodes Using Plasmonic Core-Shell Nanowires”, 2013
- Applied Physics Letters “Editors Pick”, 2013
- 30<sup>th</sup> Annual Japanese Journal of Applied Physics Paper Award, 2008
- Commendation for Excellence in Technical Communications – Laser Focus World Magazine, 2007
- Outstanding Research Achievement – Solid State Lighting and Display Center, University of California Santa Barbara, 2007
- National Research Council (NRC) Postdoctoral Associate Fellowship (declined) – NIST, 2007
- 3 year Graduate Student Support Package – University of California Santa Barbara, 2000-2003
- Departmental fellowship (Electrical Engineering) – University of California Santa Barbara, 2000
- Graduated with honors – University of California Irvine, 2000
- Finalist for senior engineer of the year – University of California Irvine, 2000

### **Leadership Roles, Memberships, Services:**

- Sources Thrust Leader for NSF Engineering Research Center on Smart Lighting
- Reviewer for Applied Physics Letters, Laser and Photonics Review, Journal of Crystal Growth, Photonics Technology Letters, Electron Device Letters, Photonics Review, and Electrochemical and Solid-State Letters
- Member – IEEE, IEEE Photonics Society, Eta Kappa Nu, American Physical Society

### **Book Chapters:**

- [1] **D. Feezell** and S. Nakamura, “Nonpolar and Semipolar Group III-Nitride Lasers,” in *Semiconductor Lasers: Fundamentals and Applications*, Edited by A. Baranov and E Tournie, Woodhead Publishing, ISBN13: 9780857091215, Apr. 2013.

### **Journal Publications:**

- [1] **D. Feezell**, Y. Sharma, and S. Krishna, “Optical Properties of Nonpolar III-Nitrides for Intersubband Photodetectors,” *J. Appl. Phys.*, vol. 113, pp. 133103(1-7), Apr. 2013.
- [2] **D. Feezell**, J. Speck, S. DenBaars, and S. Nakamura “Properties and Performance of Semipolar (2021) Group III Nitride Light-Emitting Diodes,” *J. Disp. Tech.*, vol. 9, pp. 190-198, Mar. 2013.

- [3] A. Rishinaramangalam, M. Fairchild, S. Hersee, G. Balakrishnan, and **D. Feezell**, "Three-Dimensional GaN Templates for Molecular Beam Epitaxy of Nonpolar InGaN/GaN Coaxial Light-Emitting Diodes," *J. Vac. Sci. Technol. B*, vol. 31, pp. 03C107(1-7), Feb. 2013.
- [4] S. DenBaars, **D. Feezell**, K. Kelchner, S. Pimputkar, C. Pan, C. Yen, S. Tanaka, Y. Zhao, N. Pfaff, R. Farrell, M. Iza, S. Keller, U. Mishra, J. Speck, and S. Nakamura, "Development of Gallium-Nitride-Based Light-Emitting Diodes (LEDs) and Laser Diodes for Energy-Efficient Lighting and Displays," *Acta Materialia*, vol. 61, pp. 945-951, Feb. 2013.
- [5] Y. Zhao, Q. Yan, **D. Feezell**, K. Fujito, C. Van de Walle, J. Speck, S. DenBaars, and S. Nakamura, "Optical polarization characteristics of semipolar (30 $\bar{3}$ 1) and (30 $\bar{3}$  $\bar{1}$ ) InGaN/GaN light-emitting diodes," *Opt. Express*, vol. 21, pp. A53-A59, Dec. 2012.
- [6] C. Holder, J. Speck, S. DenBaars, S. Nakamura, and **D. Feezell**, "Demonstration of Nonpolar GaN-Based Vertical Cavity Surface-Emitting Lasers," *Applied Physics Express*, vol. 5, pp. 092104(1-3), Sep. 2012.
- [7] C. Pan, T. Gilbert, N. Pfaff, S. Tanaka, Y. Zhao, **D. Feezell**, J. Speck, S. Nakamura, and S. DenBaars, "Reduction in Thermal Droop Using Thick Single-Quantum-Well Structure in Semipolar (20 $\bar{2}$ 1) Blue Light-Emitting Diodes," *Appl. Phys. Express* vol. 5, pp. 102103(1-4), Sep. 2012.
- [8] Y. Kawaguchi, C. Huang, Y. Wu, Q. Yan, C. Pan, Y. Zhao, S. Tanaka, K Fujito, **D. Feezell**, C. Van de Walle, S. DenBaars, and S. Nakamura, "Influence of Polarity on Carrier Transport in Semipolar (20 $\bar{2}$ 1) and (20 $\bar{2}$  $\bar{1}$ ) Multiple-Quantum-Well Light-Emitting Diodes," *Applied Physics Letters*, vol. 100, pp. 231110(1-4), Jun. 2012.
- [9] C. Pan, S. Tanaka, F. Wu, Y. Zhao, J. Speck, S. Nakamura, S. DenBaars, and **D. Feezell**, "High-Power, Low-Efficiency-Droop Semipolar (20 $\bar{2}$ 1) Single-Quantum-Well Blue Light-Emitting Diodes," *Applied Physics Express*, vol. 5, pp. 062103(1-3), Jun. 2012.
- [10] Y. Zhao, Q. Yan, C. Huang, S. Huang, P. Hsu, S. Tanaka, C. Pan, Y. Kawaguchi, K Fujito, C. Van de Walle, J. Speck, S. DenBaars, S. Nakamura, and **D. Feezell**, "Indium Incorporation and Emission Properties of Nonpolar and Semipolar InGaN Quantum Wells," *Applied Physics Letters*, vol. 100, pp. 201108(1-4), May 2012.
- [11] P. Hsu, M. Hardy, F. Wu, I. Koslow, E. Young, A. Romanov, K. Fujito, **D. Feezell**, S. DenBaars, J. Speck, and S. Nakamura, "444.9 nm Semipolar (1 $\bar{1}$  $\bar{2}$  $\bar{2}$ ) Laser Diodes Grown on an Intentionally Stress Relaxed InGaN Waveguiding Layer," *Applied Physics Letters*, vol. 100, pp. 021104(1-4), Jan. 2012.
- [12] C. Huang, M. Hardy, K. Fujito, **D. Feezell**, J. Speck, S. DenBaars, and S. Nakamura, "Demonstration of 505 nm Laser Diodes Using Wavelength-Stable (20 $\bar{2}$ 1) InGaN/GaN Quantum Wells," *Applied Physics Letters*, vol. 99, pp. 241115(1-3), Dec. 2011.
- [13] R. Farrell, D. Haeger, P. Hsu, K. Fujito, **D. Feezell**, S. DenBaars, J. Speck, and S. Nakamura, "Determination of Internal Parameters for AlGaIn-Cladding-Free *m*-Plane InGaN/GaN Laser Diodes," *Applied Physics Letters*, vol. 99, pp. 171115(1-3), Oct. 2011.

- [14] R. Farrell, D. Haeger, P. Hsu, M. Schmidt, K. Fujito, **D. Feezell**, S. DenBaars, J. Speck, and S. Nakamura, "High-Power Blue-Violet AlGa<sub>N</sub>-Cladding-Free *m*-Plane InGa<sub>N</sub>/Ga<sub>N</sub> Laser Diodes," *Applied Physics Letters*, vol. 99, pp. 171113(1-3), Oct. 2011.
- [15] C. Huang, Q. Yan, Y. Zhao, K. Fujito, **D. Feezell**, C. Van de Walle, J. Speck, S. DenBaars, and S. Nakamura, "Influence of Mg-Doped Barriers on Semipolar (2021) Multiple-Quantum-Well Green Light-Emitting Diodes," *Applied Physics Letters*, vol. 99, pp. 141114(1-3), Oct. 2011.
- [16] M. Hardy, **D. Feezell**, S. DenBaars, and S. Nakamura, "Group III-Nitride Lasers: A Materials Perspective," *Materials Today*, vol. 14, pp. 408-415, Sep. 2011.
- [17] R. Farrell, D. Haeger, P. Hsu, M. Hardy, K. Kelchner, K. Fujito, **D. Feezell**, U. Mishra, S. DenBaars, J. Speck, and S. Nakamura, "AlGa<sub>N</sub>-Cladding-Free *m*-plane InGa<sub>N</sub>/Ga<sub>N</sub> Laser Diodes with p-Type AlGa<sub>N</sub> Etch Stop Layers," *Applied Physics Express*, vol. 4, pp. 092105(1-3), Sep. 2011.
- [18] Y. Zhao, S. Tanaka, Q. Yan, C. Huang, R. Chung, C. Pan, K. Fujito, **D. Feezell**, C. Van de Walle, J. Speck, S. DenBaars, and S. Nakamura, "High Optical Polarization Ratio from Semipolar (2021) Blue-Green InGa<sub>N</sub>/Ga<sub>N</sub> Light-Emitting Diodes," *Applied Physics Letters*, vol. 99, pp. 051109(1-3), Aug. 2011.
- [19] Y. Zhao, S. Tanaka, C. Pan, K. Fujito, **D. Feezell**, J. Speck, S. DenBaars, and S. Nakamura, "High-Power Blue-Violet Semipolar (2021) InGa<sub>N</sub>/Ga<sub>N</sub> Light-Emitting Diodes with Low Efficiency Droop at 200 A/cm<sup>2</sup>," *Applied Physics Express*, vol. 4, pp. 082104(1-3), Jul. 2011.
- [20] **D. Feezell**, M. Schmidt, S. DenBaars, and S. Nakamura, "Development of Nonpolar and Semipolar InGa<sub>N</sub>/Ga<sub>N</sub> Visible Light-Emitting Diodes," Invited Article *MRS Bulletin: Nonpolar and Semipolar Group III Nitride-Based Materials*, vol. 34, pp. 318-323, May 2009.
- [21] A. Tyagi, H. Zhong, R. Chung, **D. Feezell**, M. Saito, K. Fujito, J. Speck, S. DenBaars, and S. Nakamura, "InGa<sub>N</sub>/Ga<sub>N</sub> Laser Diodes on Semipolar (1011) Bulk Ga<sub>N</sub> Substrates," *Phys. Stat. Sol. (c)*, vol. 5, pp. 2108-2110, Mar. 2008.
- [22] **D. Feezell**, J. Speck, S. DenBaars, and S. Nakamura, "Nonpolar Gallium Nitride Laser Diodes Are The Next New Blue," Invited Article *Laser Focus World Magazine*, vol. 43, pp. 79-83, Oct. 2007.
- [23] R. Farrell, **D. Feezell**, M. Schmidt, D. Haeger, K. Kelchner, K. Iso, H. Yamada, M. Saito, K. Fujito, D. Cohen, J. Speck, S. DenBaars, and S. Nakamura, "Continuous-Wave Operation of AlGa<sub>N</sub>-Cladding-Free Nonpolar *m*-plane InGa<sub>N</sub>/Ga<sub>N</sub> Laser Diodes," *Japanese Journal of Applied Physics Express Letters*, vol. 46, pp. L761-L763, Aug. 2007.
- [24] A. Tyagi, H. Zhong, R. Chung, **D. Feezell**, M. Saito, K. Fujito, J. Speck, S. DenBaars, and S. Nakamura, "Semipolar (1011) InGa<sub>N</sub>/Ga<sub>N</sub> Laser Diodes on Bulk Ga<sub>N</sub> Substrates," *Japanese Journal of Applied Physics Express Letters*, vol. 46, pp. L444-L445, May 2007.
- [25] **D. Feezell**, R. Farrell, M. Schmidt, H. Yamada, M. Ishida, S. DenBaars, D. Cohen, and S. Nakamura, "Thin Metal Intra-Cavity Contact and Lateral Current-Distribution Scheme for Ga<sub>N</sub>-Based Vertical-Cavity Lasers," *Applied Physics Letters*, vol. 90, pp. 181128(1-3), May 2007.

- [26] **D. Feezell**, M. Schmidt, R. Farrell, K. Kim, M. Saito, K. Fujito, D. Cohen, J. Speck, S. DenBaars, and S. Nakamura, "AlGa<sub>N</sub>-Cladding-Free Nonpolar InGa<sub>N</sub>/Ga<sub>N</sub> Laser Diodes," *Japanese Journal of Applied Physics Express Letters*, vol. 46, pp. L284-L286, Mar. 2007.
- [27] M. Schmidt, K. Kim, R. Farrell, **D. Feezell**, D. Cohen, M. Saito, K. Fujito, J. Speck, S. DenBaars, and S. Nakamura, "Demonstration of Nonpolar m-plane InGa<sub>N</sub>/Ga<sub>N</sub> Laser Diodes," *Japanese Journal of Applied Physics Express Letters*, vol. 46, pp. L190-L191, Feb. 2007.
- [28] M. Mehta, **D. Feezell**, D. Buell, A. Jackson, L. Coldren, and J. Bowers, "Electrical Design Optimization of Single-Mode Tunnel Junction-Based Long-Wavelength VCSELs," *IEEE Journal of Quantum Electronics*, vol. 42, no. 7, pp. 675-682, Jul. 2006.
- [29] **D. Feezell**, D. Buell, D. Lofgreen, M. Mehta, and L. Coldren, "Optical Design of InAlGaAs Low-Loss Tunnel-Junction Apertures for Long-Wavelength Vertical Cavity Lasers," *IEEE Journal of Quantum Electronics*, vol. 42, no. 5, pp. 494-499, May 2006.
- [30] D. Buell, **D. Feezell**, and L. Coldren, "Molecular Beam Epitaxy of InP-Based Alloys for Long-Wavelength Vertical-Cavity Lasers," *Journal of Vacuum Science Technology B*, vol. 24, no. 3, pp. 1544-1547, May 2006.
- [31] **D. Feezell**, L. Johansson, D. Buell, and L. Coldren, "Efficient Modulation of InP-Based 1.3 $\mu$ m VCSELs with AsSb-Based DBRs," *IEEE Photonics Technology Letters*, vol. 17, no. 11, pp. 2253-2255, Nov. 2005.
- [32] **D. Feezell**, D. Buell, and L. Coldren, "InP-Based 1.3 – 1.6 $\mu$ m VCSELs with Selectively Etched Tunnel-Junction Apertures on a Wavelength Flexible Platform," *IEEE Photonics Technology Letters*, vol. 17, no. 10, pp. 2017-2019, Oct. 2005.
- [33] **D. Feezell**, D. Buell, and L. Coldren, "Continuous Wave Operation of All-Epitaxial InP-Based 1.3 $\mu$ m VCSELs with 57% Differential Quantum Efficiency," *Electronics Letters*, vol. 41, no. 14, pp. 803-04, Jul. 2005.
- [34] M.H.M. Reddy, T. Asano, **D. Feezell**, D. Buell, A. Huntington, R. Koda, and L. Coldren, "Selectively Etched Tunnel Junction for Lateral Current and Optical Confinement in InP-Based Vertical Cavity Lasers," *Journal of Electronic Materials*, vol. 33, no. 2, pp. 118-22, Feb. 2004.
- [35] T. Asano, **D. Feezell**, R. Koda, M.H.M. Reddy, D. Buell, A. Huntington, E. Hall, S. Nakagawa, and L. Coldren, "InP-Based All-Epitaxial 1.3 $\mu$ m VCSELs with Selectively Etched AllInAs Apertures and Sb-Based DBRs," *IEEE Photonics Technology Letters*, vol. 15, no. 10, pp. 1333-5, Oct. 2003.
- [36] M.H.M. Reddy, D. Buell, **D. Feezell**, T. Asano, R. Koda, A. Huntington, and L. Coldren, "Continuous-Wave Operation of 1.55 $\mu$ m Vertical-Cavity Surface-Emitting Laser with Digital-Alloy Active Region Using Submonolayer Superlattices," *IEEE Photonics Technology Letters*, vol. 15, no. 7, pp. 891-3, Jul. 2003.
- [37] M.H.M. Reddy, D. Buell, T. Asano, R. Koda, **D. Feezell**, A. Huntington, and L. Coldren, "Lattice-matched Al<sub>0.95</sub>Ga<sub>0.05</sub>AsSb Oxide for Current Confinement in InP-Based Long Wavelength VCSELs," *Journal of Crystal Growth*, vol. 251, Apr., 2003.

- [38] M.H.M. Reddy, D. Buell, A. Huntington, T. Asano, R. Koda, **D. Feezell**, D. Lofgreen, and L. Coldren, "Al<sub>0.95</sub>Ga<sub>0.05</sub>As<sub>0.56</sub>Sb<sub>0.44</sub> for Lateral Oxide-Confinement Layer in InP-Based Devices," *Applied Physics Letters*, vol. 82, no. 9, pp. 1329-31, Mar. 2003.

### **Conference Presentations:**

- [1] **D. Feezell**, Y. Sharma, and S. Krishna, "Optical Properties of Nonpolar III-Nitrides for Intersubband Photodetectors," *International Conference on Nitride Semiconductors 2013*, Washington D.C., Aug. 2013.
- [2] M. Nami, A. Rishinaramangalam, and **D. Feezell**, "Analysis of Light Extraction Efficiency for GaN-Based Coaxial Microwall Light-Emitting Diodes," *International Conference on Nitride Semiconductors 2013*, Washington D.C., Aug. 2013.
- [3] Y. Zhao, C. Y. Huang, C. C. Pan, S. Tanaka, Y. Kawaguchi, K. Fujito, **D. Feezell**, J. S. Speck, S. P. DenBaars, and S. Nakamura, "Semipolar (2021) InGaN Light-Emitting Diodes and Laser Diodes," *International Workshop on Nitride Semiconductors 2012*, Sapporo, Japan, Oct. 2012.
- [4] C. Holder, **D. Feezell**, J. S. Speck, S. P. DenBaars, and S. Nakamura, "Demonstration of nonpolar GaN-based vertical cavity surface-emitting lasers," *International Workshop on Nitride Semiconductors 2012*, Sapporo, Japan, Oct. 2012.
- [5] C. C. Pan, S. Tanaka, F. Wu, Y. Zhao, J. S. Speck, S. Nakamura, S. P. DenBaars, and **D. Feezell**, "High-Power, Low-Efficiency-Droop Semipolar (2021) Single-Quantum-Well Blue Light-Emitting Diodes," *International Workshop on Nitride Semiconductors 2012*, Sapporo, Japan, Oct. 2012.
- [6] M.T. Hardy, N. Pfaff, Q. Yan, I. Koslow, P. S. Hsu, **D. Feezell**, S. Nakamura, J. Speck, and S. DenBaars, "Increased Polarization Ratio for Green (2021) Light Emitting Diodes Grown on a 1D Relaxed In-GaN Buffer Layer," *International Workshop on Nitride Semiconductors 2012*, Sapporo, Japan, Oct. 2012.
- [7] C. Y. Huang, M. T. Hardy, Y. Zhao, Q. Yan, A. Pourhashemi, **D. F. Feezell**, J. S. Speck, S. P. DenBaars, and S. Nakamura, "Semipolar (2021) Blue to Aquamarine Laser Diodes with Minimal Wavelength Blueshift," *International Workshop on Nitride Semiconductors 2012*, Sapporo, Japan, Oct. 2012.
- [8] C. Y. Huang, Y. Zhao, F. Wu, Y. Kawaguchi, **D. F. Feezell**, S. P. DenBaars, J. S. Speck, and S. Nakamura, "Growth characteristics of InGaN/GaN quantum wells on semipolar (2021) and (2021) planes," *International Workshop on Nitride Semiconductors 2012*, Sapporo, Japan, Oct. 2012.
- [9] C. Y. Huang, Y. Zhao, Q. Yan, Y. Kawaguchi, Y. R. Wu, **D. F. Feezell**, C. G. Van de Walle, J. S. Speck, S. P. DenBaars, and S. Nakamura, "Carrier transports in semipolar multiple-quantum well light-emitting diodes," *International Workshop on Nitride Semiconductors 2012*, Sapporo, Japan, Oct. 2012.
- [10] P. S. Hsu, M. T. Hardy, F. Wu, I. Koslow, E. C. Young, A. Romanov, K. Fujito, **D. F. Feezell**, S. P. DenBaars, J. S. Speck, and S. Nakamura, "Stress Relaxed III-Nitride Based Semipolar (1122) Lasers," *International Workshop on Nitride Semiconductors 2012*, Sapporo, Japan, Oct. 2012.

- [11] **D. Feezell**, C. Holder, J. Speck, S. DenBaars, and S. Nakamura, "Electrically-Injected Nonpolar GaN-Based Vertical-Cavity Surface-Emitting Lasers", *2012 International Symposium on Compound Semiconductors (late news)*, Santa Barbara, Aug. 2012.
- [12] Y. Zhao, Q. Yan, K. Fujito, **D. Feezell**, S. DenBaars, J. Speck, C. Van de Walle, and S. Nakamura, "Optical Polarization Characteristics on Semipolar (30-31) and (30-3-1) InGaN/GaN Light-Emitting Diodes", *2012 International Symposium on Compound Semiconductors*, Santa Barbara, Aug. 2012.
- [13] M. Hardy, P. Hsu, I. Koslow, **D. Feezell**, S. Nakamura, J. Speck, and S. DenBaars, "Demonstration of a Relaxed Waveguide Semipolar (2021) InGaN/GaN Laser Diode," *2012 Conference on Laser and Electro-Optics (CLEO)*, San Jose, May. 2012.
- [14] Y. Zhao, C. Huang, S. Tanaka, C. Pan, K. Fujito, **D. Feezell**, J. Speck, S. DenBaars, and S. Nakamura, "Semipolar (2021) Blue and Green InGaN Light-Emitting Diodes," *2012 Conference on Laser and Electro-Optics (CLEO)*, San Jose, May. 2012.
- [15] C. Huang, Y. Zhao, M. Hardy, **D. Feezell**, J. Speck, S. DenBaars, and S. Nakamura, "Semipolar (2021) Laser Diodes ( $\lambda = 505$  nm) with Wavelength-Stable InGaN/GaN Quantum Wells," *2012 Conference on Laser and Electro-Optics (CLEO)*, San Jose, May. 2012.
- [16] **D. Feezell**, Y. Zhao, C. Pan, S. Tanaka, C. Huang, F. Wu, J. Speck, S. DenBaars, and S. Nakamura, "Development and Status of Nonpolar/Semipolar Light-Emitting Diodes," *NSF-KAUST-UCSB Workshop on Solid-State Lighting*, Saudi Arabia, Feb. 2012.
- [17] **D. Feezell** and S. Nakamura, "Low-Droop and High Efficiency Semipolar (2021) Light-Emitting Diodes," *2012 SPIE Photonics West Conference*, San Francisco, Feb. 2012.
- [18] Y. Zhao, S. Tanaka, R. Chung, C. Pan, K. Fujito, **D. Feezell**, C. Van de Walle, J. Speck, S. DenBaars, and S. Nakamura, "Highly Polarized Spontaneous Emission from Semipolar (2021) InGaN/GaN Light-Emitting Diodes," *Electronic Materials Conference*, Santa Barbara, Jun. 2011.
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